

isc N-Channel MOSFET Transistor

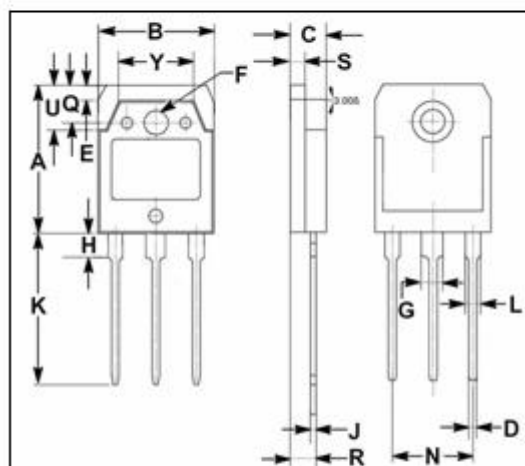
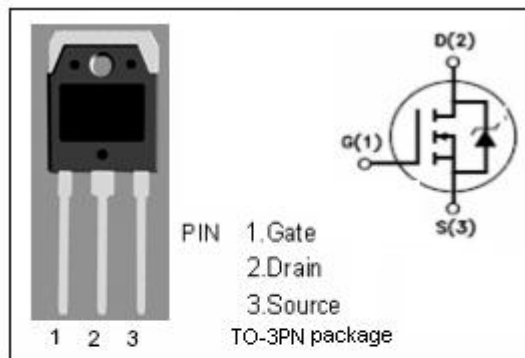
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DESCRIPTION

- Drain Current $-I_D=9A@ T_C=25^{\circ}C$
- Drain Source Voltage:
: $V_{DSS}=800V(\text{Min})$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	800	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C=25^{\circ}C$	9	A
P_{tot}	Total Dissipation@ $T_C=25^{\circ}C$	150	W
T_j	Max. Operating Junction Temperature	80	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

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• ELECTRICAL CHARACTERISTICS (T_c=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
_(BR) DSS	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 1mA	800			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.5	3.5	5.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D =4A		1.0	1.5	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =800V; V _{GS} = 0			500	uA
t _{on}	Turn-on time	V _{GS} =10V; I _D =9A;		280	425	ns
t _{off}	Turn-off time	R _L =25Ω		460	690	ns
V _{SD}	Diode Forward Voltage	I _F =9A; V _{GS} =0		1.05	1.58	V